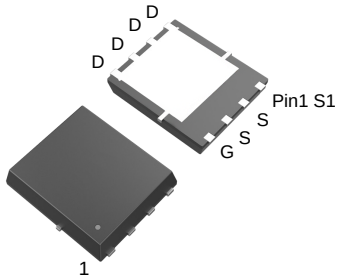
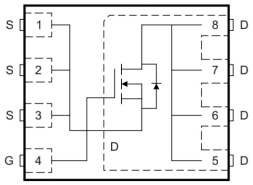
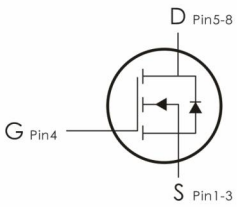
Description：

This N-Channel MOSFET uses advanced SGT technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.







Features：

1) V_{DS}=150V,I_D=90A,$R_{DS(ON)}$<9mΩ @V_{GS}=10V（Typ：7.8mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity SGT technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.
6) MSL3

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
NI009TFG	I009TF	DFN5*6-8	5000 pcs/Reel

Absolute Maximum Ratings：(T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current [1]	90	A
	Continuous Drain Current-T_C=100℃ [1]	63	
I_{DM}	Pulsed Drain Current [2]	360	
P_D	Power Dissipation	138	W
E_{AS}	Single pulse avalanche energy [3]	51	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\Theta JC}$	Thermal Resistance,Junction to Case	0.9	℃/W
$R_{\Theta JA}$	Thermal Resistance,Junction to Ambient	50	℃/W

Electrical Characteristics: (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	150	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=150V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics (Note3)						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	2	3	4	V
$R_{DS(ON)}$	Drain-Source On Resistance [4]	V_{GS}=10V,I_D=20A	---	7.8	9	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=75V, V_{GS}=0V, f=1MHz	---	2100	---	pF
C_{oss}	Output Capacitance		---	619	--	
C_{rss}	Reverse Transfer Capacitance		---	23	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=75V, I_D=20A, R_G=4.7Ω ,V_{GS}=10V	---	21	---	ns
t_r	Rise Time		---	20	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	13	---	ns
t_f	Fall Time		---	12	---	ns
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=75V, I_D=20A	---	30	---	nC
Q_{gs}	Gate-Source Charge		---	11	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	7.8	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=20A	---	0.9	1.2	V
I_S	Continuous Drain Current	V_D=V_G=0V	---	---	75	A
I_{SM}	Pulsed Drain Current		---	---	300	A
Trr	Reverse Recovery Time	I_F=20A,T_J=25℃ dI/dt=100A/us	---	78	---	ns
Qrr	Reverse Recovery Charge		---	170	---	nC

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=75V,V_G=10V,L=0.5mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics: (T_C=25℃ unless otherwise noted)

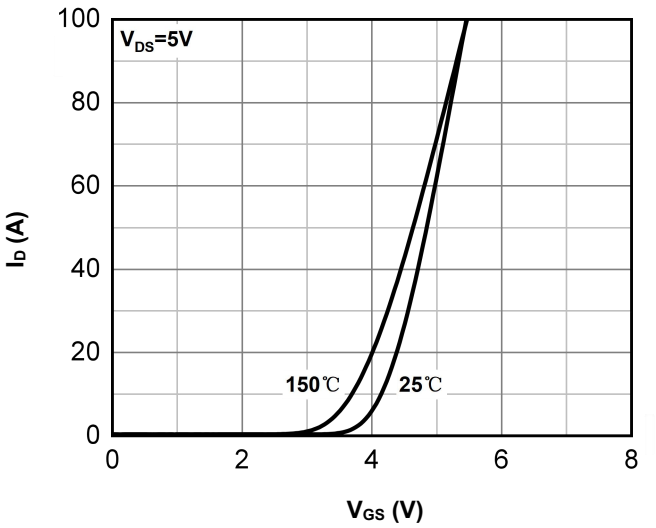


Fig.1 Typ. transfer characteristics

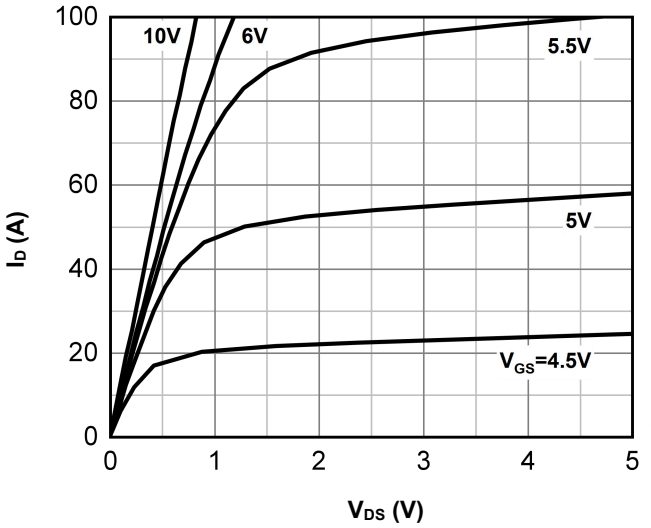


Fig.2 Typ. output characteristics

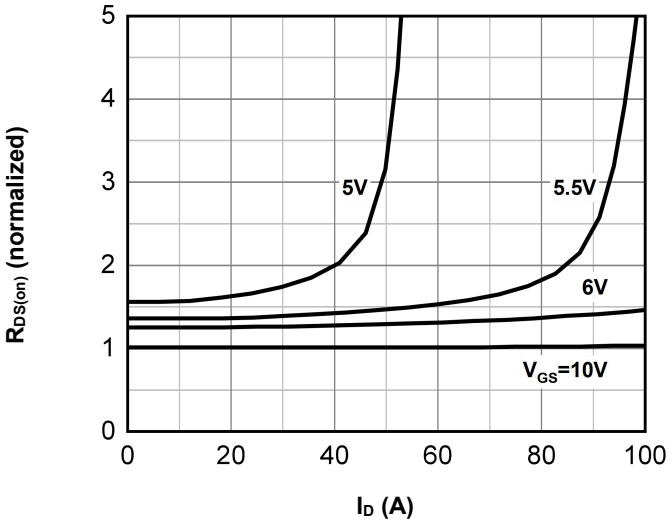


Fig.3 Normalized on-resistance vs drain current

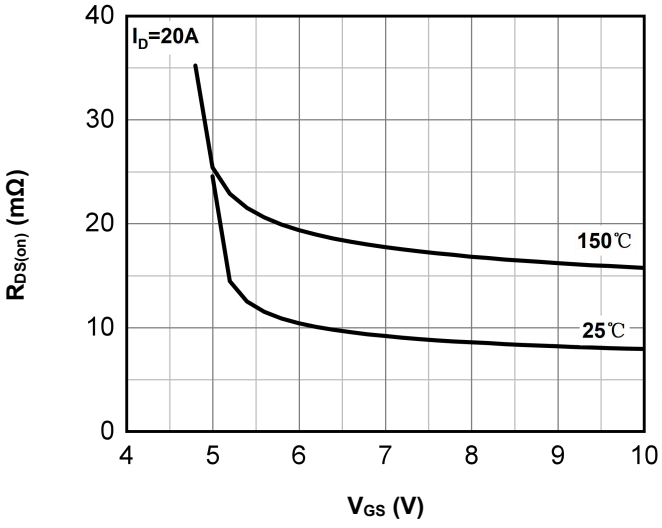


Fig.4 Typ. on-resistance vs gate-source voltage

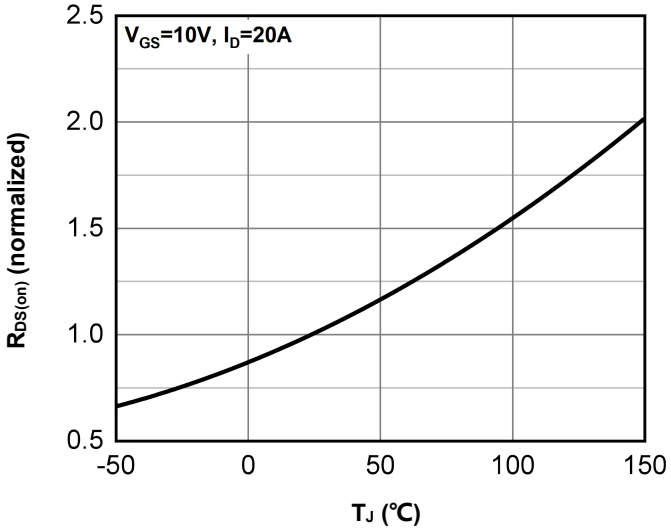


Fig.5 Normalized on-resistance vs junction temperature

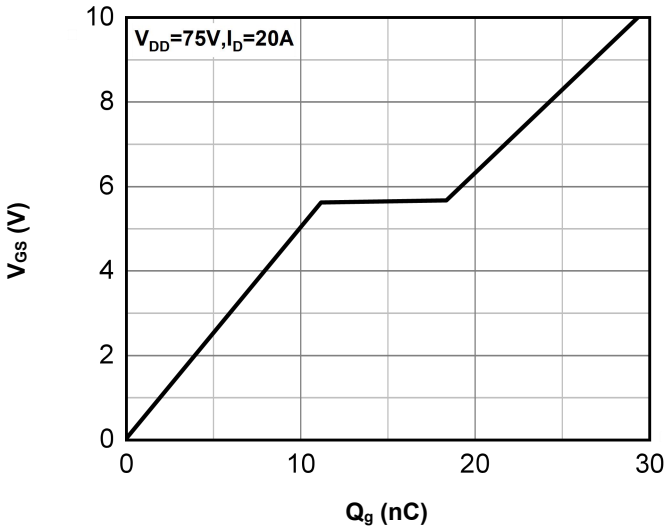


Fig.6 Typ. gate charge

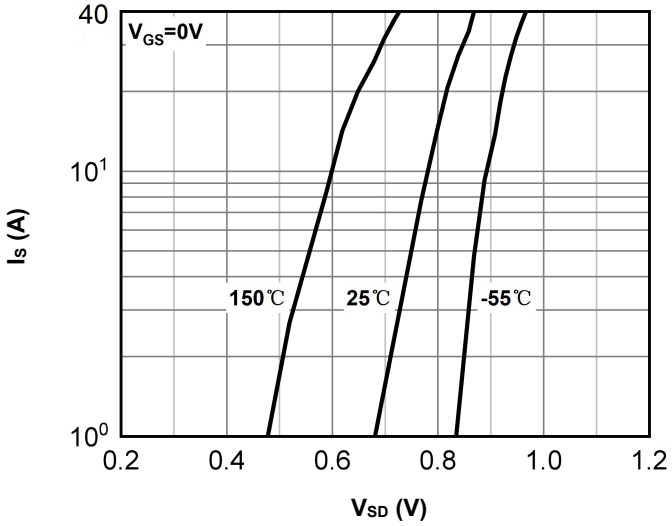


Fig.7 Typ. forward characteristics of body diode

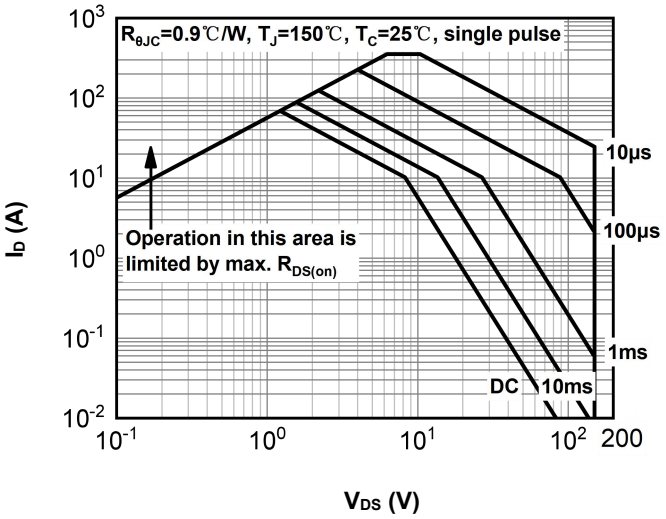


Fig.8 Safe operating area

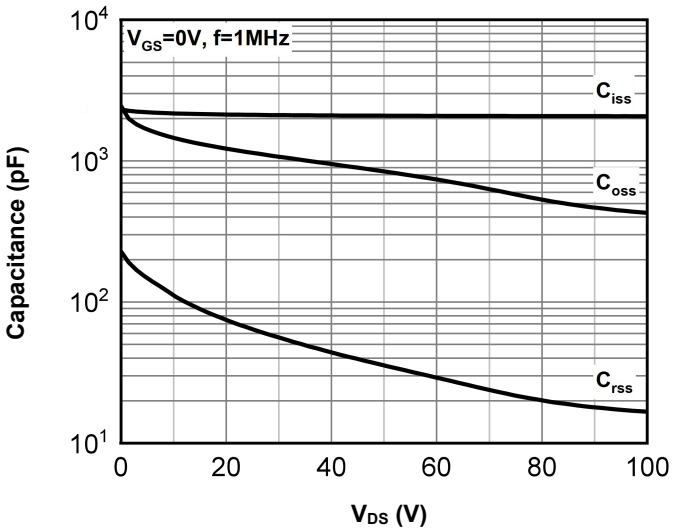


Fig.9 Typ. Capacitance

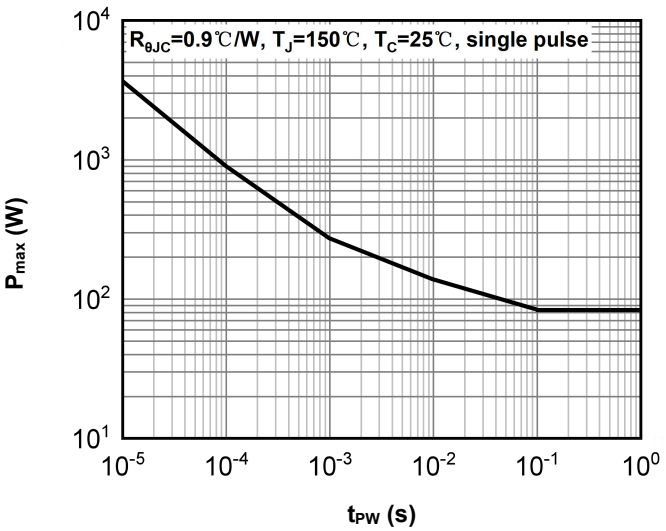


Fig.10 Single pulse maximum power dissipation

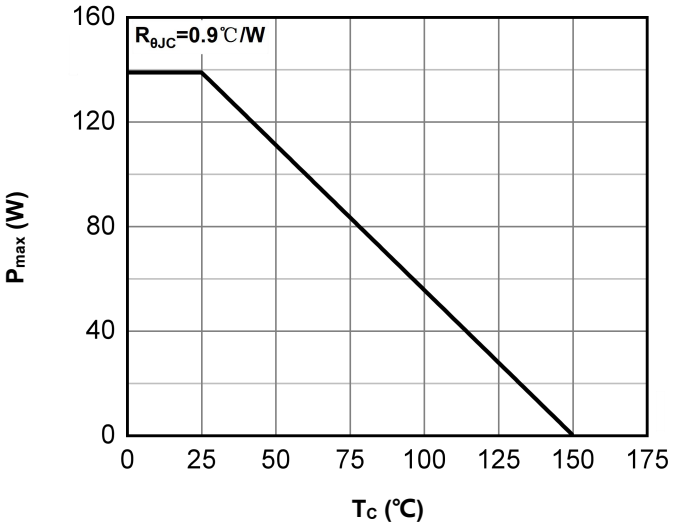


Fig.11 Max. power dissipation vs case temperature

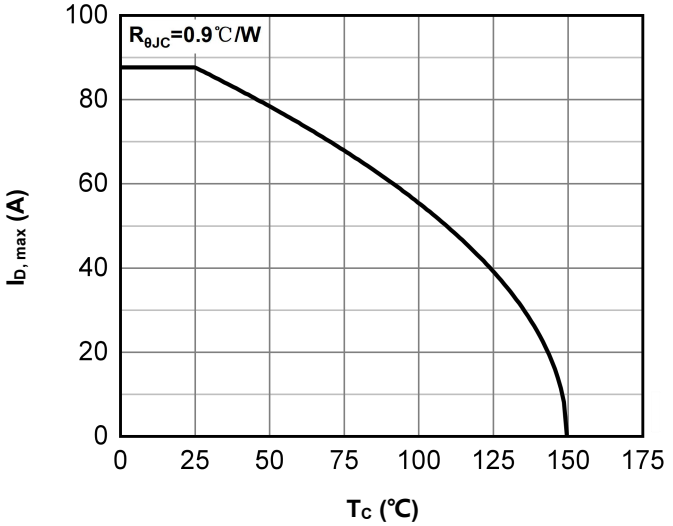


Fig.12 Max. continuous drain current vs case temperature

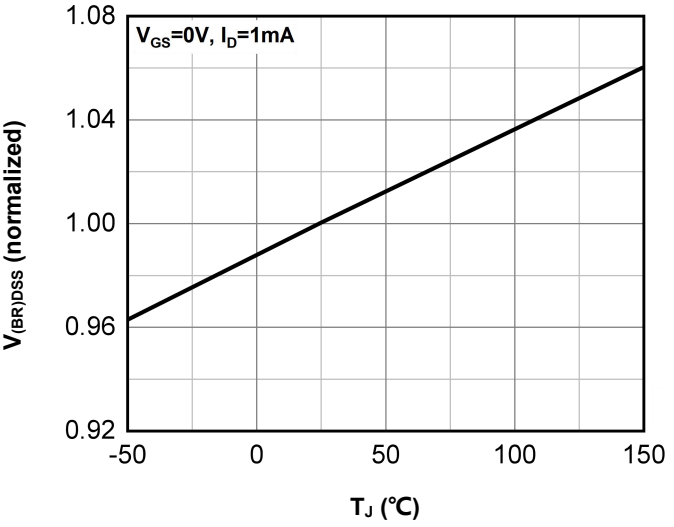


Fig.13 Normalized $V_{(BR)DSS}$ vs junction temperature

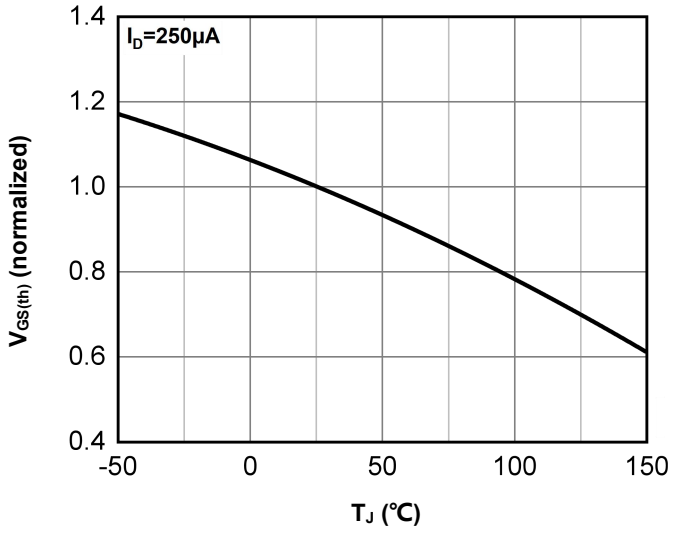


Fig.14 Normalized $V_{GS(th)}$ vs junction temperature

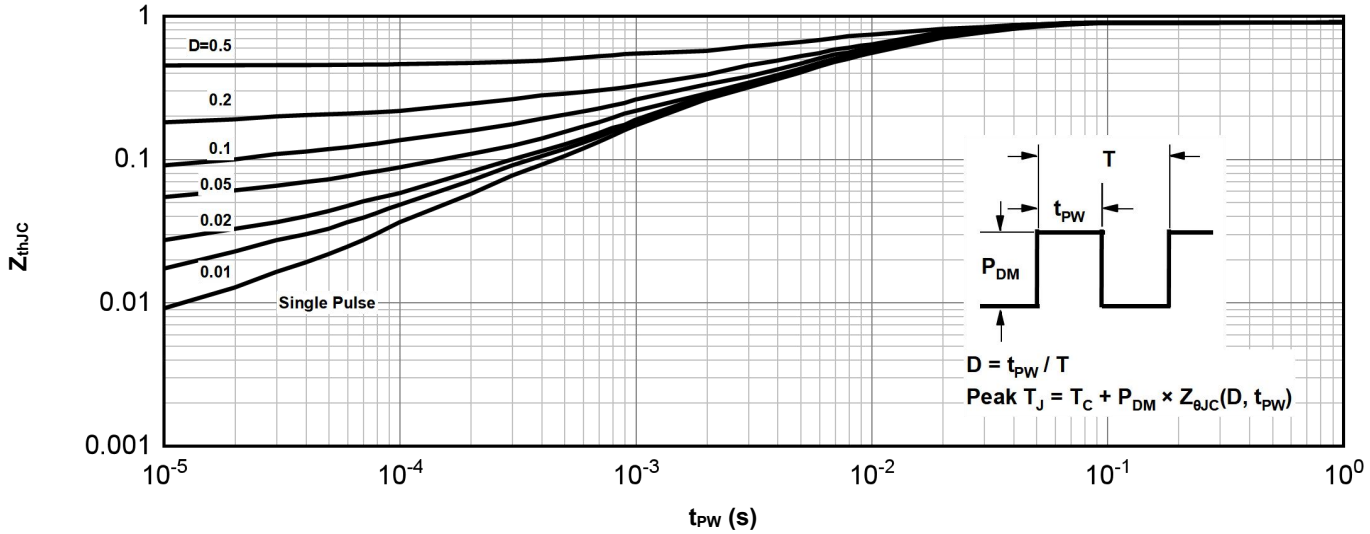
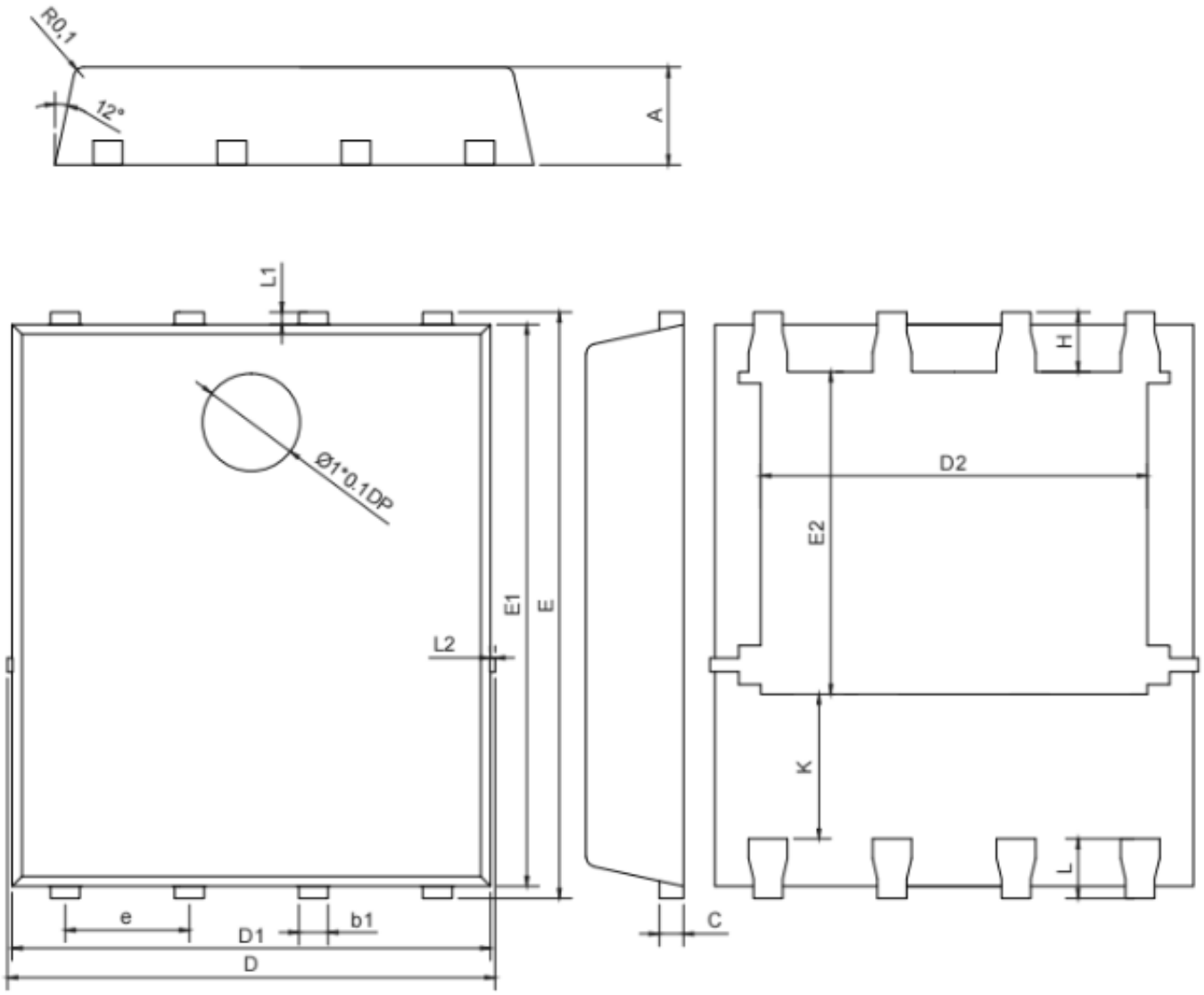


Fig.15 Transient thermal impedance from junction to case

DFN5X6-8 Package Information：

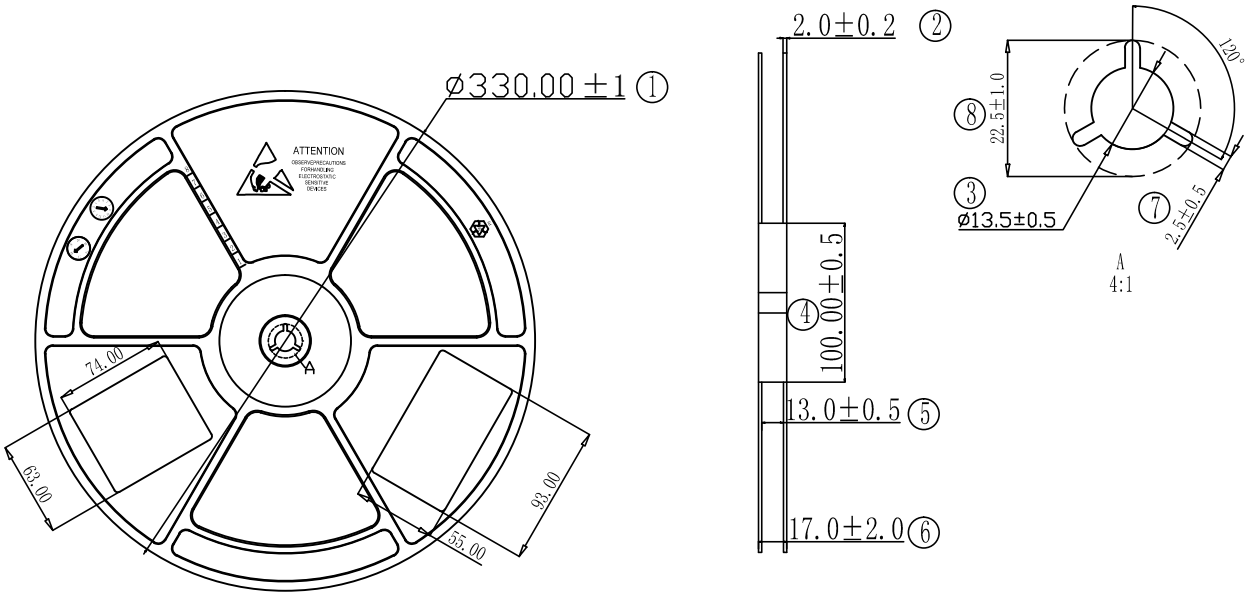


Dimensions

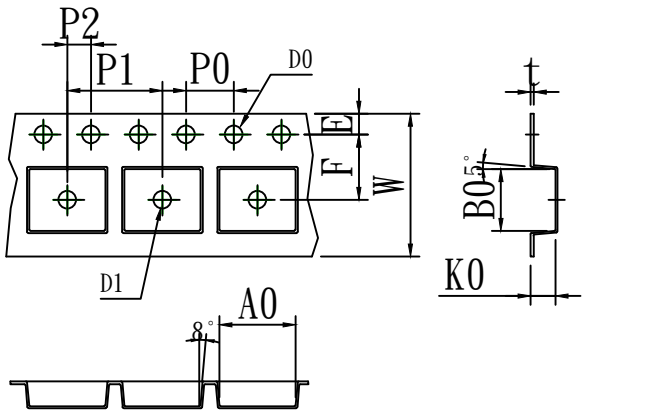
Unit	A	b	b1	c	D	D1	D2	e	E	E1	E2	H	K	L	L1	L2
mm	0.90 (1.00) 1.10	0.35 (0.40) 0.45	0.20 (0.30) 0.40	0.20 (0.25) 0.35	4.85 (5.05) 5.25	4.80 (4.90) 5.30	3.80 (4.10) 4.40	1.17 (1.27) 1.37	5.80 (6.00) 6.20	5.50 (5.75) 6.00	3.10 (3.35) 3.60	0.50 (0.65) 0.80	1.10 -- --	0.51 (0.61) 0.71	0.05 (0.12) 0.20	-- -- 0.10

Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15±0.10	5.40±0.10	1.30±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.00±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Marking Information：

①. Doingter LOGO

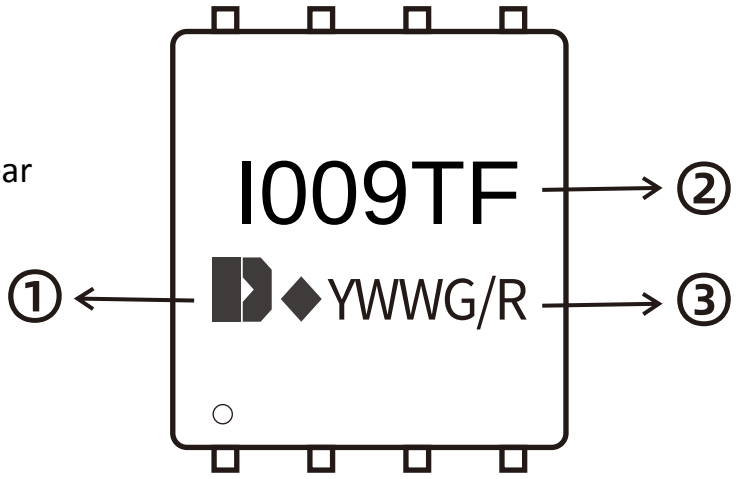
②. Part NO.

③. Date Code(YWWG / R)

Y：Year Code，last digit of the year

WW：Week Code(01-53)

G/R：G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2025-09-06	Release of final version

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